

## **RFMD® Announces Qualification of Second Gallium Nitride (GaN) Process Technology**

GREENSBORO, N.C., May 10, 2010 (GlobeNewswire via COMTEX News Network) -- RF Micro Devices, Inc. today announced the successful qualification of RFMD's second high-power Gallium Nitride (GaN) process technology, expanding the Company's industry-leading portfolio of compound semiconductor technologies.

RFMD's second high-power GaN HEMT process technology (GaN2) achieves 1 to 2 dB higher gain and 6 dB greater linearity than RFMD's first high-power GaN process technology (GaN1) at moderately lower power density.

RFMD's GaN2 targets CATV broadband transmission products and other multi-market applications and is optimized for higher linearity, higher gain and lower voltage operation. RFMD's first high-power GaN process technology (GaN1) was qualified in the June 2009 quarter and delivers much higher power density and voltage breakdown than competing technologies.

RFMD's GaN1 is ideally suited for high-performance devices such as power amplifiers for radar and communications.

RFMD's GaN2 reliability measurements confirm a useful lifetime of over 17 million hours at a channel temperature of 200 deg C. This industry-leading reliability performance is especially noteworthy because GaN2 is an early stage process on RFMD's GaN technology development roadmap. Additional technologies in development include MMIC process modules with complimentary Integrated Passive Component (IPC) technology.

Bob Van Buskirk, president of RFMD's Multi-Market Products Group (MPG), said, "RFMD's high-performance GaN technology is consistently demonstrating industry-leading levels of reliability, allowing our customers to design GaN products that exceed their stringent system reliability specifications. RFMD's GaN technology also enables advanced RF components and products that operate at significantly lower power consumption levels, helping to satisfy the rapidly increasing end-market requirements for energy saving 'green technologies.'"

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